

IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A nanoprobe, comprising:

a substrate having a dielectric layer integrally formed thereon, the dielectric layer forming a rigid projected portion, which extends beyond an end of the substrate to overhang the substrate; and

a plurality of conductive lines adhered integrally formed to on the projected portion, the conductive lines and further extending beyond an end of the projected portion by a distance to overhang the projected portion and to form contact points, wherein the lines are connected to material of the projected portion to provide stiffness and the contact points provide flexibility during use of the nanoprobe.

2. (Cancelled) The nanoprobe as recited in claim 1, wherein the layer includes a dielectric layer and the dielectric layer forms the projected portion.

3. (Currently Amended) The nanoprobe as recited in claim 12, wherein the substrate includes silicon and the dielectric layer includes at least one of silicon nitride and silicon oxide.

4. (Original) The nanoprobe as recited in claim 1, wherein the conductive lines include a thickness of between about 1% and about 10% of a thickness of the projected portion.

5. (Original) The nanoprobe as recited in claim 1, wherein the conductive lines are formed from a noble metal.

6. (Original) The nanoprobe as recited in claim 1, wherein the conductive lines are formed from one or more of Ag, Au, Pt, Ir, Ru, Pd and their alloys.

7. (Original) The nanoprobe as recited in claim 1, wherein the conductive lines each have a thickness and a width, which are 300 nm, or less.

8. (Original) The nanoprobe as recited in claim 1, wherein the conductive lines include a pitch of less than or equal to one micron.

9. (Original) The nanoprobe as recited in claim 8, wherein the pitch is less than or equal to 600 nm.

10. (Original) The nanoprobe as recited in claim 1, wherein the nanoprobe includes circuitry formed thereon.

11. (Currently Amended) A nanoprobe for making electrical measurements, comprising:
- a substrate;
- a dielectric layer integrally formed on the substrate and extending beyond an edge of the substrate to overhang the substrate to and form a rigid projected portion;
- a plurality of conductive lines integrally formed on and extending beyond at least over the projected portion without contacting the substrate, the conductive lines being adhered to the projected portion; the conductive lines further extending beyond an end of the projected portion by a distance to form contact points, wherein the lines are connected to the projected portion to provide stiffness and the contact points provide flexibility during use of the nanoprobe.
12. (Original) The nanoprobe as recited in claim 11, wherein the substrate includes silicon and the dielectric layer includes at least one of silicon nitride and silicon oxide.
13. (Original) The nanoprobe as recited in claim 11, wherein the conductive lines include a thickness of between about 1% and about 10% of a thickness of the projected portion.
14. (Original) The nanoprobe as recited in claim 11, wherein the conductive lines are formed from a noble metal.
15. (Original) The nanoprobe as recited in claim 11, wherein the conductive lines are

formed from one or more of Ag, Au, Pt, Ir, Ru, Pd and their alloys.

16. (Original) The nanoprobe as recited in claim 11, wherein the conductive lines each have a thickness and a width, which are 300 nm, or less.

17. (Original) The nanoprobe as recited in claim 11, wherein the conductive lines include a pitch of less than or equal to one micron.

18. (Original) The nanoprobe as recited in claim 17, wherein the pitch is less than or equal to 600 nm.

19. (Original) The nanoprobe as recited in claim 11, wherein the nanoprobe includes circuitry formed thereon.

Claims 20-29 (Canceled)